

SP4T 10 W/50 W_{peak} Power Switch 1 MHz to 6.0 GHz

Features

- Frequency Range 1 MHz to 6.0 GHz
- Low insertion loss:
0.30 dB @ 1.0 GHz
0.70 dB @ 3.0 GHz
0.80 dB @ 6.0 GHz
- High isolation:
25 dB @ 3.0 GHz
21 dB @ 5.0 GHz
- 10 W CW Power, 50 W_{peak} Peak Power
- Low power consumption, less than 1 mW
- No external DC blocking capacitors on RF lines
- All RF ports OFF state
- Versatile 2.6 V – 5.25 V power supply
- No need to supply negative voltages

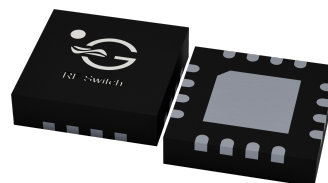


Figure 1: TS8242FK in 3.0 x 3.0 mm² QFN 16-pin package.

Applications

- Private mobile and defense radios
- Public safety handsets
- Cellular infrastructure
- Satellite terminals
- Datalinks

General Description

The TS8242FK is a 2nd Generation symmetrical reflective Single Pole Four Throw (SP4T) switch designed for medium power switching applications. The TS8242FK covers 1 MHz to 6.0 GHz bandwidth and provides low insertion loss, high isolation, and high linearity within a small package size. With 10 W CW power handling and 50 W_{peak} peak power capability, the TS8242FK is well suited for demanding applications requiring superior RF performance.

The TS8242FK is housed in a compact 3.0×3.0 mm² 16-lead Quad Flat No-lead (QFN) plastic package.

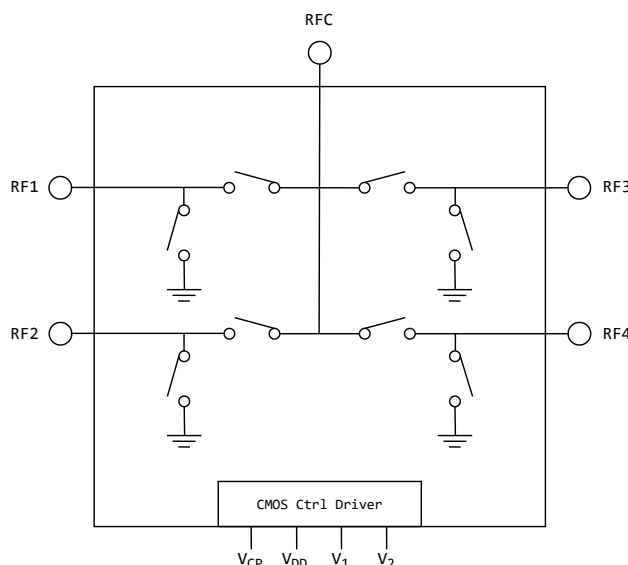


Figure 2: TS8242FK functional diagram



RoHS10/REACH/Halogen free

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Ordering information

Table 1: Ordering Information

Device Part Number	Package Type	Notes
TS8242FK	16 Pin 3.0x3.0x0.75 mm ³ QFN	Core part number
TS8242FK-EVB	Evaluation Board	
TS8242FKMTRPBF ¹	330 mm reel, 3 000 pcs	Full reel

¹ MTRPBF - M: Manufacturing, TR: Tape and Reel, and PBF: lead free.

Table 2: Tape and Reel Information

Form	Quantity	Reel Diameter	Reel Width
Tape and Reel	3 000	13" (330mm)	18mm

Pin Assignment

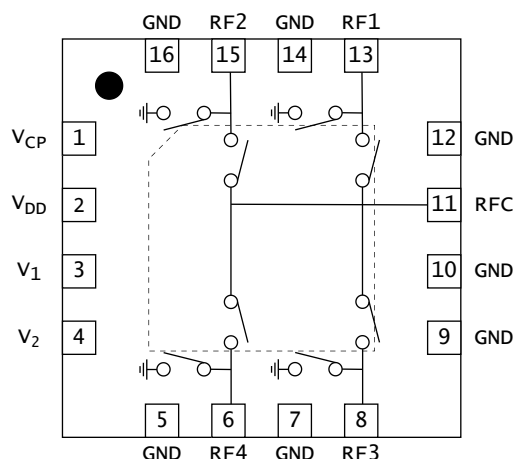


Figure 3: TS8242FK pin assignment [top view]

Table 3: Pin Definition

Pin Number	Pin Name	Description
1	V _{CP}	Internal charge pump voltage output, connect a 1nF capacitor to GND on this node.
2	V _{DD}	DC Power Supply
3	V ₁	Switch control input 1
4	V ₂	Switch control input 2
6	RF4	RF port 4
8	RF3	RF port 3
11	RFC	RF Common port (ANT)
13	RF1	RF port 1
15	RF2	RF port 2
5,7,9,10,12,14,16	GND	Connect to ground ²
17 ¹	GND	Ground thermal pad, please connect to GND

¹ The backside ground (thermal) pad of the package must be grounded directly to the ground plane of PCB with multiple vias, and adequate heat sinking must be used to ensure proper operation and thermal management.

² These pins are NC pins inside the package. To avoid floating pins around RF lines, we request these to be connected to ground.

Absolute Maximum Ratings

Table 4: Absolute Maximum Ratings $T_A = +25^{\circ}\text{C}$ unless otherwise specified¹.

Parameter	Symbol	Value	Unit
Electrical Ratings			
Power Supply Voltage	V_{DD}	5.5	V
External bias voltage on V_{CP} pin	V_{CP}	-20	V
Storage Temperature Range	T_{st}	-55 – 125	$^{\circ}\text{C}$
Operating Temperature Range	T_{op}	-40 – 85	$^{\circ}\text{C}$
Maximum Junction Temperature	T_j	+140	$^{\circ}\text{C}$
Maximum RF CW input power ³	RFx/RFC	44	dBm
Maximum RF peak input power, 1% duty cycle, 10 μs pulse ²	RFx/RFC	49	dBm
Thermal Ratings			
Thermal Resistance (junction-to-case) – Bottom side	$R_{\theta jc}$	9.9	$^{\circ}\text{C}/\text{W}$
Soldering Temperature	T_{solder}	+260	$^{\circ}\text{C}$
ESD Ratings			
Human Body Model (HBM)	Level 1B	500 – <1000	V
Charged Device Model (CDM)	Level C3	≥ 1000	V
Moisture Rating			
Moisture Sensitivity Level ⁴	MSL	1	

¹ Maximum ratings are absolute ratings. Exposure to absolute maximum rating conditions for extended periods may affect device reliability and can cause permanent damage to the device. Exceeding one or a combination of the absolute maximum ratings may cause permanent and irreversible damage to the device and/or to surrounding circuit. Functional operation of the device is not implied in any conditions above those indicated in the Electrical Specifications section.

² Test frequency 800 MHz.

³ See Power De-rating table for low frequencies.

⁴ Tagore recommends to store parts in moisture barrier bag to preserve solderability.

Electrical Specifications

Table 5: Electrical Specifications $T_A = +25^{\circ}\text{C}$; $V_{DD} = +3.3\text{V}$; 50Ω Source/Load.

Parameter	Condition	Minimum	Typical	Maximum	Unit
Operating frequency	f	1		6000	MHz
Insertion loss	30MHz		0.25		dB
unmatched, upto 4.0 GHz	1.0GHz		0.30	0.40	dB
RFC – RFx	3.0GHz		0.60		dB
	4.0GHz		0.85		dB
Insertion loss ¹	30MHz		0.20		dB
matched upto 6.0 GHz	1.0GHz		0.30		dB
RFC – RFx	3.0GHz		0.70		dB
	5.0GHz		0.70		dB
	6.0GHz		0.80		dB
Isolation	30MHz		60		dB
unmatched, upto 4.0 GHz	1.0GHz		35		dB
RFC – RFx	3.0GHz		25		dB
	4.0GHz		23		dB
Isolation ¹	30MHz		60		dB
matched upto 6.0 GHz	1.0GHz		37		dB
RFC – RFx	3.0GHz		27		dB
	5.0GHz		21		dB
	6.0GHz		18		dB

¹ Matched values are not guaranteed as they include performance of matching components. These components are beyond control of TagoreTech and therefore given values are indications, not guaranteed values.

Table 6: Electrical Specifications $T_A = +25^\circ\text{C}$; $V_{DD} = +3.3\text{V}$; 50Ω Source/Load.

Parameter	Condition	Minimum	Typical	Maximum	Unit
Operating frequency	f	1		6000	MHz
Return Loss	30MHz		-30		dB
unmatched, upto 4.0 GHz	1.0GHz		-30		dB
RFC – RFx	3.0GHz		-15		dB
	4.0GHz		-12		dB
Return Loss ¹	30MHz		-30		dB
matched upto 6.0 GHz	1.0GHz		-30		dB
RFC – RFx	3.0GHz		-12		dB
	5.0GHz		-16		dB
	6.0GHz		-15		dB

¹ Matched values are not guaranteed as they include performance of matching components. These components are beyond control of TagoreTech and therefore given values are indications, not guaranteed values.

Table 7: Electrical Specifications $T_A = +25^\circ\text{C}$; $V_{DD} = +3.3\text{V}$; 50Ω Source/Load.

Parameter	Condition	Minimum	Typical	Maximum	Unit
Operating frequency	f	1		6000	MHz
Harmonic Distortion					
H_2	800MHz, $P_{in} = 40\text{dBm}$		-86		dBc
H_3	800MHz, $P_{in} = 40\text{dBm}$		-89		dBc
IIP3	800MHz		74		dBm
Power and Compression point					
P_{maxCW}^2	Max RF CW Power	40	42		dBm
P_{maxpeak}	Max RF Peak Power		48		dBm
$P_{0.1\text{dB}}$	800MHz, CW	40	43		dBm
$P_{\text{peak}0.1\text{dB}}$	800MHz, 1% duty cycle, $10\mu\text{s}$ pulse	45	48		dBm
$P_{1\text{dB}}^1$	800MHz, CW		45		dBm
$P_{\text{maxhot RFX}}^5$	Max RF CW Power, hot switching		37		dBm
$P_{\text{maxhot RFC}}^5$	Max RF CW Power, hot switching		37		dBm

¹ $P_{1\text{dB}}$ has been given for comparison reasons only. Please do not exceed Absolute Maximum ratings.² See Power De-rating table⁵ Dependent on thermal design and surrounding circuits.

Table 8: Electrical Specifications $T_A = +25^\circ\text{C}$; $V_{DD} = +3.3\text{V}$; 50Ω Source/Load.

Parameter	Condition	Minimum	Typical	Maximum	Unit
Operating frequency	f	1		6000	MHz
Noise					
CP switching noise ⁴	RBW=1kHz		-140		dBm
Switching Time					
t_{ON} ⁸	Switch ON time		0.7	1.3	μs
t_{OFF} ⁸	Switch OFF time		0.6	1.2	μs
t_{RISE} ⁸	Switch RISE time		0.5	0.7	μs
t_{FALL} ⁸	Switch FALL time		0.5	0.9	μs
t_{wON}	Minimum Switch ON time		3.6		μs
t_{wOFF}	Minimum Switch OFF time		3.6		μs
$f_{PRR}, C_{VCP} = 1\text{nF}^3$	Maximum pulse repetition rate		1		kHz
$f_{PRR}, C_{VCP} = 10\text{nF}^3$	Maximum pulse repetition rate		1.4		kHz
$f_{PRR}, C_{VCP} = 100\text{nF}^3$	Maximum pulse repetition rate		1.8		kHz
$f_{PRR}, V_{CP\text{ext}} = -18\text{V}^6$	Maximum pulse repetition rate		>20		kHz
$t_{startup}, C_{VCP} = 1\text{nF}^3$	startup time		0.8		ms
$t_{startup}, C_{VCP} = 10\text{nF}^3$	startup time		7		ms
$t_{startup}, C_{VCP} = 100\text{nF}^3$	startup time		40		ms
Power Supply, DC					
Control voltage	Power Supply V_{DD}	2.6	3.3	5.25	V
	All control pins high, V_{ih} ⁷	1.0	3.3	5.25	V
	All control pins low, V_{il}	-0.3	0	0.5	V
Control current	All control pins high, I_{ih}			7.5	μA
	All control pins low, I_{il}		0		μA
Current consumption	I_{DD} , active mode (V_{DD} on)		160	260	μA

³ With internal charge pump and with C_{VCP} .⁴ Above 250 MHz. For operation at VHF frequencies, below 250 MHz, consider charge pump bypass switch version, if charge pump noise is critical for your application. Please contact TagoreTech for more information.⁶ External -18 V applied to V_{CP} pin.⁷ Control voltage V_{ih} cannot be higher than V_{DD} (to avoid forward biasing of ESD diode)⁸ Switching time characterization done at 30 Hz and 500 Hz pulse repetition rate (rate to change switch state, for example between RFC-RF1 and RFC-RF2).

Switching time definition

Example of the definition by using 10 W/40 dBm signal. We apply 10W signal to RF port, stabilized with isolator. Isolator is needed as our switch shows to RF port approximately 4Ω impedance. Let's assume that the switch insertion loss is 0.3 dB. Therefore 90% of the RF signal is 39.55 dBm and 10% of the RF signal is 1W/30dBm. We need to take into account 0.3dB insertion loss, therefore numbers are 39.25 dBm and 29.7 dBm respectively. We change the control from low to high and our time reference point is when our control signal exceeds lower threshold value V_{ihlow} . In certain measurements when control signal rise time is significantly shorter than RF output signal, we approximate start of the clock with the 50% point of the control signal.

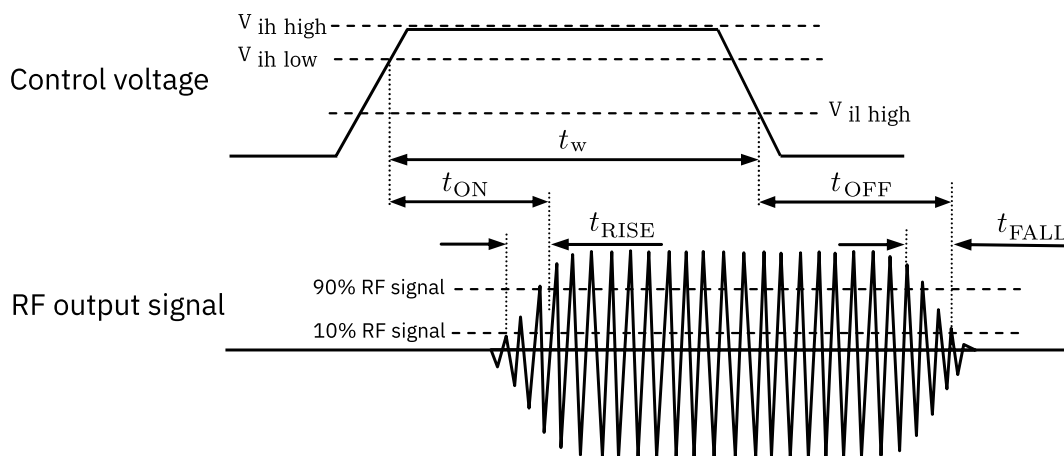


Figure 4: Switching time definition, t_{ON} , t_{OFF} , t_{RISE} , t_{FALL} . Minimum pulse width t_w .

Our component uses integrated charge pump. Maximum pulse repetition rate defines what is maximum frequency for switching events. Please do not exceed given maximum frequency. By feeding external -18 V to V_{CP} , one can improve maximum pulse repetition rate f_{PRR} . Feeding external -18 V to V_{CP} , one can drive switch at least to 20 kHz f_{PRR} . Expect current consumption of 10 mA from the -18 V supply.

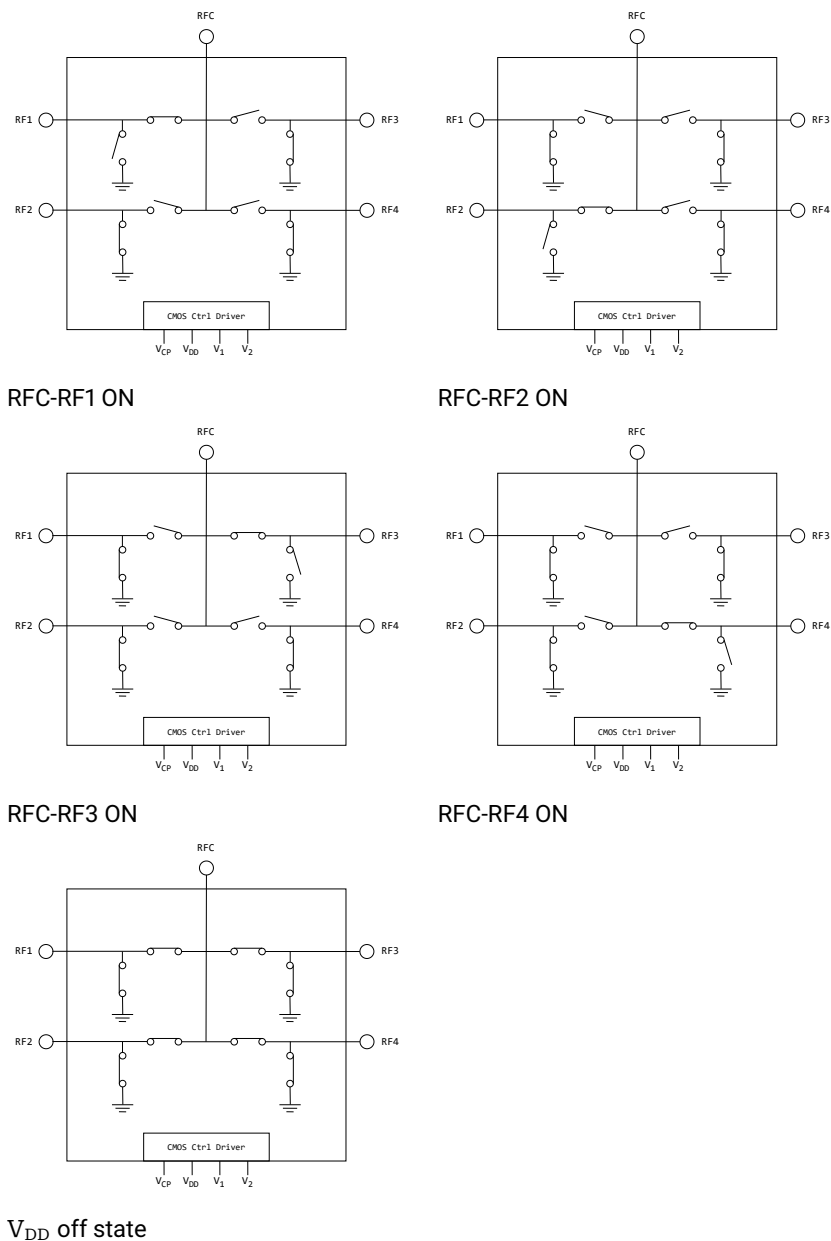
Switch Control table

Table 9: Switch Control Table

V_{DD}^1	V_2	V_1	Switch state
1	0	0	RFC – RF1 ON ²
1	0	1	RFC – RF2 ON
1	1	0	RFC – RF3 ON
1	1	1	RFC – RF4 ON
0	0	0	V_{DD} off (Isolation), all FETs are on, short shown to RFC and RF ports

¹ V_{DD} should be applied first before V_1 and V_2 , otherwise may cause damage to the device.

² There are internal pull-downs to ground on both V_1 and V_2 control pins, the state at start-up without any control voltage applied will be RFC – RF1 ON.



Theory of Operation

Isolation modes

TS8242FK has one isolation mode, VDD off mode.

Device powered off

When V_{DD} is 0V, all switch RF transistors are on, ie. every MOSFET is on. This means that series MOSFETs and shunt MOSFETs are conducting. Every RF port is essentially connected to ground, including ANT port. This is practical when device is directly connected to ANT, there is certain protection against induced electrical fields. This can partially protect radio equipment against electrical fields, when device is not in usage.

Applications

TS8242FK is offering 10 W/50 W_{peak} capability from 1 MHz to 6.0 GHz frequency band. Applications include narrowband and multi-octave wideband radios, jammers, EMC testing, public mobile radios, industrial and scientific applications. In the past, such applications were covered with power hungry and complex PIN diodes, TS8242FK significantly reduces design complexity for such RF switching needs. TS8242FK works well up to 4.0 GHz frequency without external matching components, for frequency above 4.0 GHz, matching is recommended. Datasheet provides an example matching and its performance.

Schematics and Evaluation Board

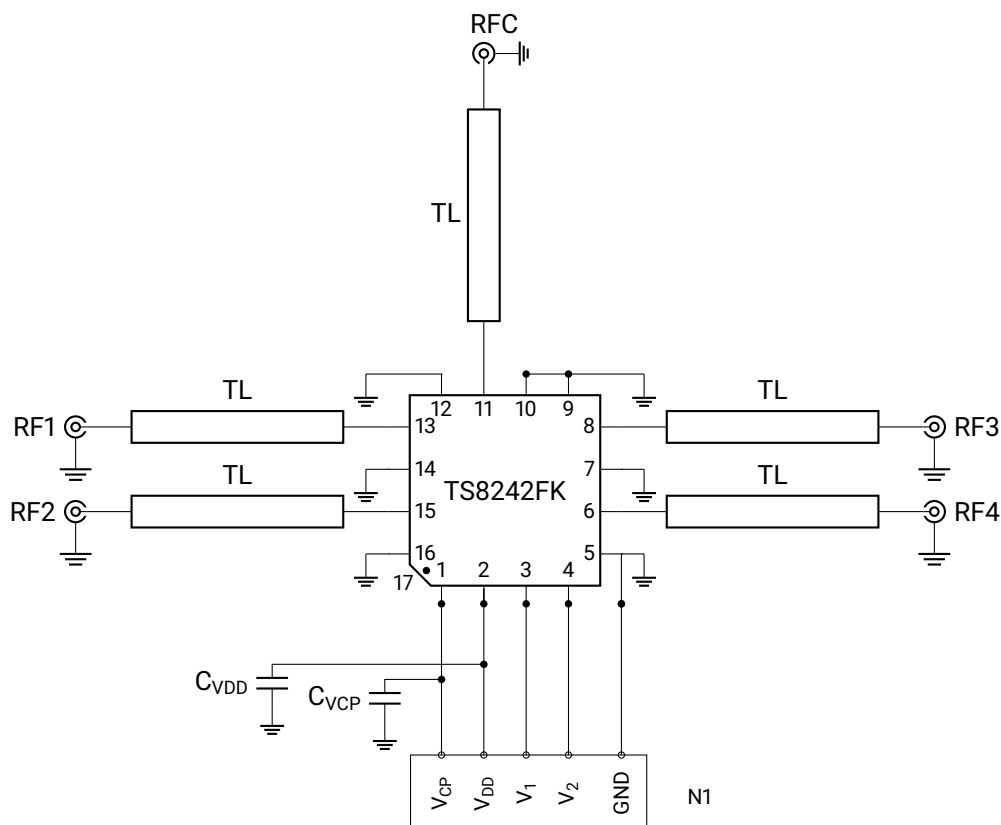
S-parameters of the both presented EVBs can be downloaded from link: [Download TS8242FK S-parameters](#)

Table 10: Port definitions in s-parameter files and plots.

PIN name	Port numbers	S-parameters	Function
RFC	1	S11	
RF1	2	S22	
RF2	3	S33	
RF3	4	S44	
RF4	5	S55	
RF10N	12	S21	RFC-RF1 ON
RF20N	13	S31	RFC-RF2 ON
RF30N	14	S41	RFC-RF3 ON
RF40N	15	S51	RFC-RF4 ON

Performance upto 4.0 GHz, unmatched

TS8242FK shows usable performance upto 4.0 GHz frequency without any matching components. Only two external components are recommended, 1 nF for V_{CP} and 10 nF for V_{DD} lines.



Schematics of TS8242FK EVB without matching components

Table 11: Components used for TS8242FK EVB

Reference	Part number / Value	Description	Notes
C_{VDD}	10 nF	Capacitor	
C_{VCP}	1 nF	Capacitor	

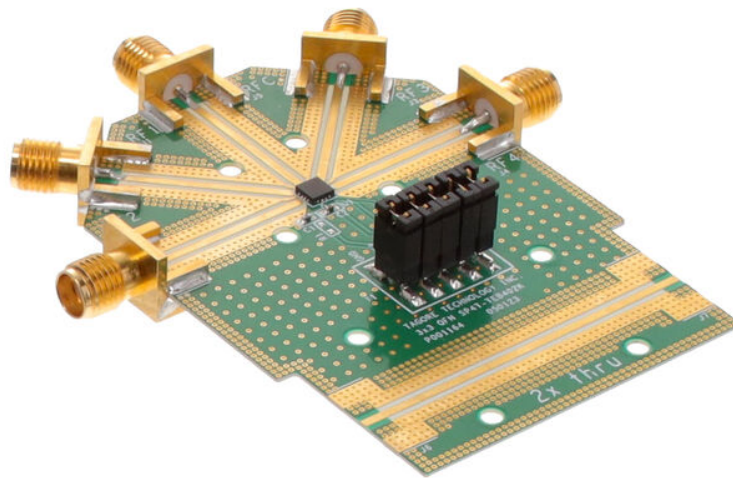
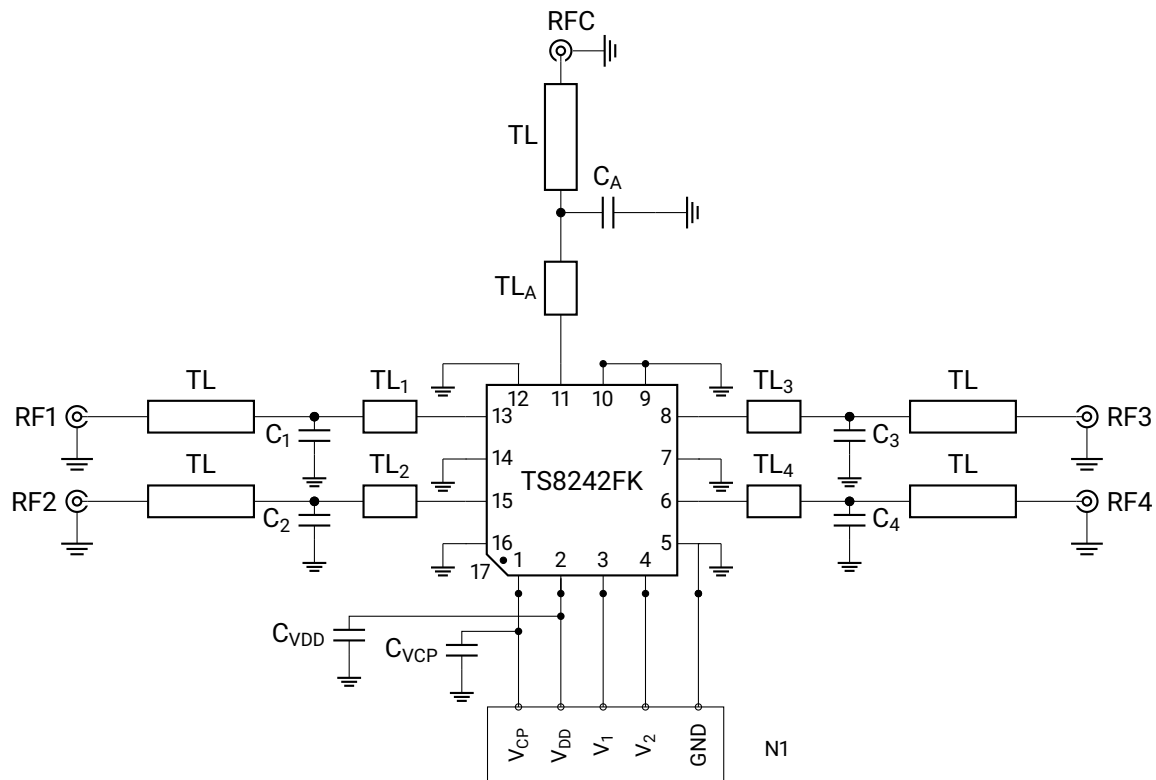


Photo of TS8242FK EVB

Performance upto 6.0 GHz, matched



Schematics of TS8242FK EVB with matching components

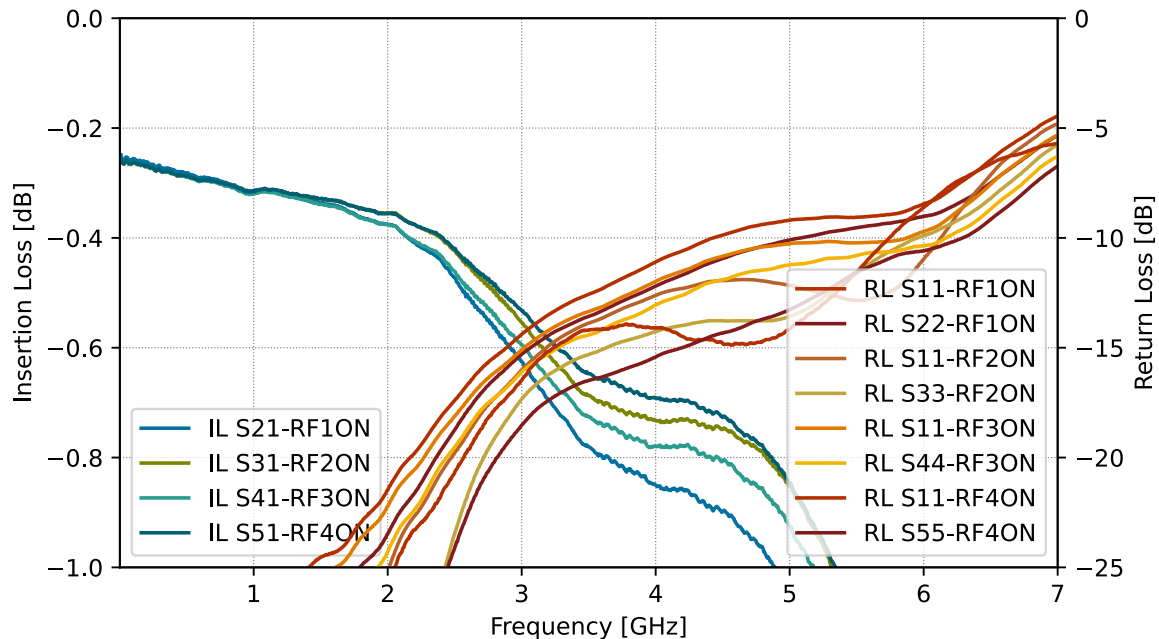
Table 12: Matching components used for 6.0 GHz performance

Reference	Part number / Value	Description	Notes
TL _A	2.1 mm	CPW length	Edge of SW to center of capacitor
C _A	0603N0R3BW251	Ceramic capacitor	0.3pF, 250V, ± 0.1pF
TL ₁	1.5 mm	CPW length	Edge of SW to center of capacitor
C ₁	0603N0R2BW251	Ceramic capacitor	0.2pF, 250V, ± 0.1pF
TL ₂	0.3 mm	CPW length	Edge of SW to center of capacitor
C ₂	0603N0R2BW251	Ceramic capacitor	0.2pF, 250V, ± 0.1pF
TL ₃	1.5 mm	CPW length	Edge of SW to center of capacitor
C ₃	0603N0R2BW251	Ceramic capacitor	0.2pF, 250V, ± 0.1pF
TL ₄	0.3 mm	CPW length	Edge of SW to center of capacitor
C ₄	0603N0R2BW251	Ceramic capacitor	0.2pF, 250V, ± 0.1pF
C _{VDD}	10 nF	Capacitor	
C _{VCP}	1 nF	Capacitor	

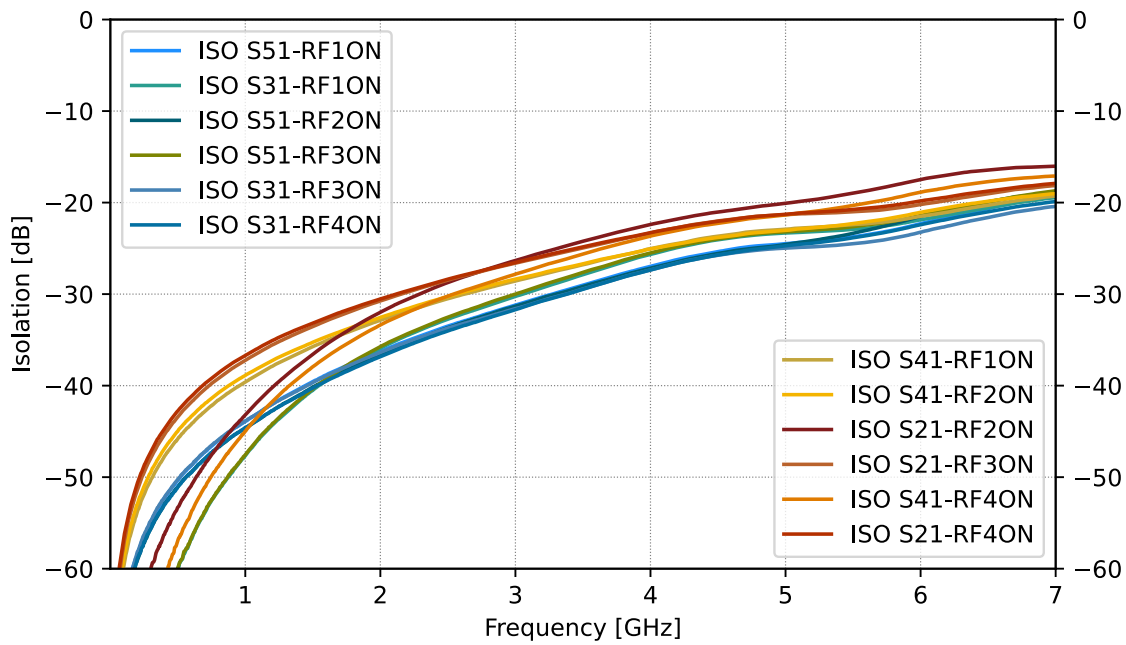
Typical characteristics

Performance upto 4.0 GHz, unmatched

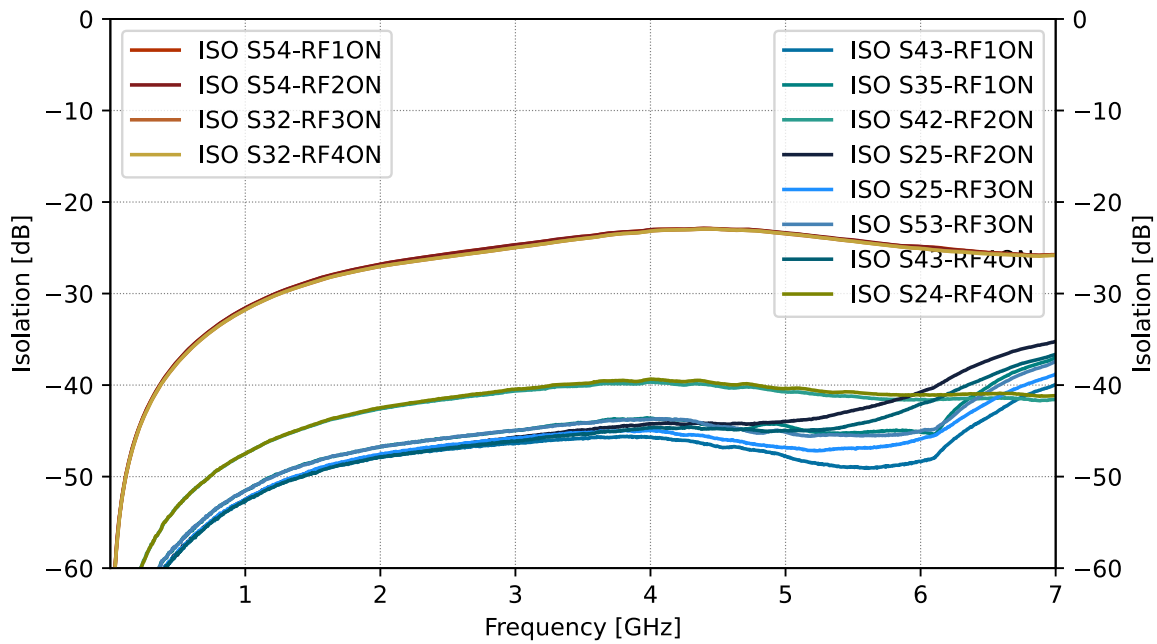
These measurements have been taken from TS8242FK EVK, CPW losses have been de-embedded from the measurements. Device does not require any matching components for operation upto 4.0 GHz. Going above 4.0 GHz, performance can be improved by adding matching to ports. Our matching example shows excellent performance upto 6.0 GHz.



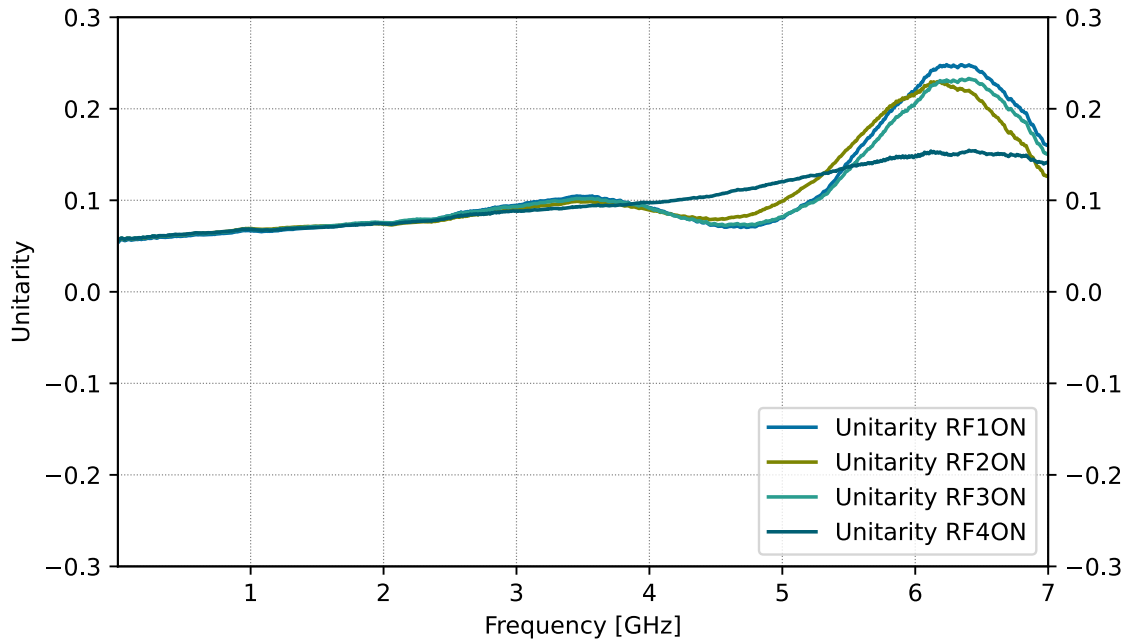
Insertion loss and Return loss, RFC – RFx.



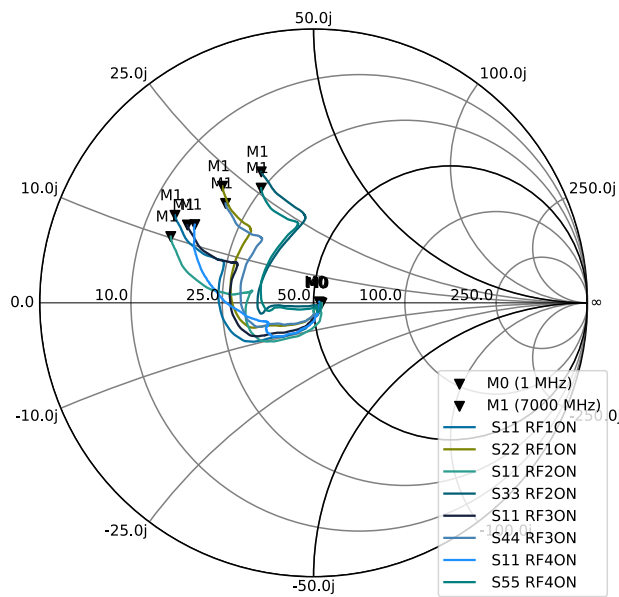
RFC – RFx isolation of non-active ports.



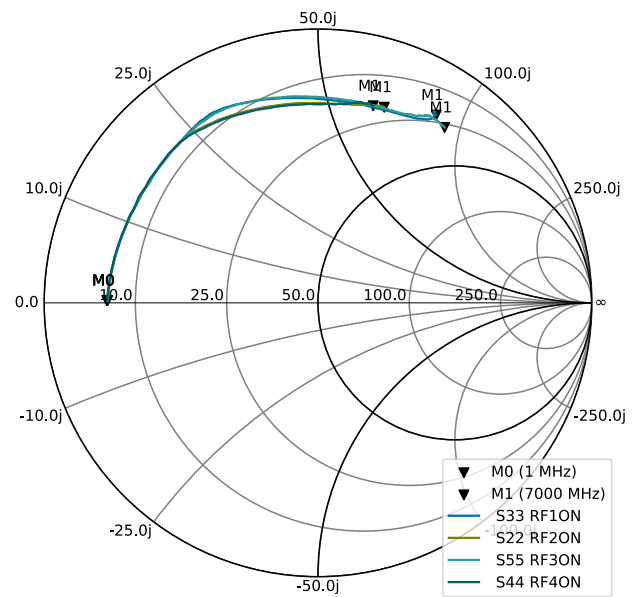
RFx – RFx isolation of non-active ports. Red/orange color curves are adjacent paths.



Unitarity, power absorption of the component, $1 - |S_{11}|^2 - |S_{21}|^2 - |S_{31}|^2 - |S_{41}|^2 - |S_{51}|^2$



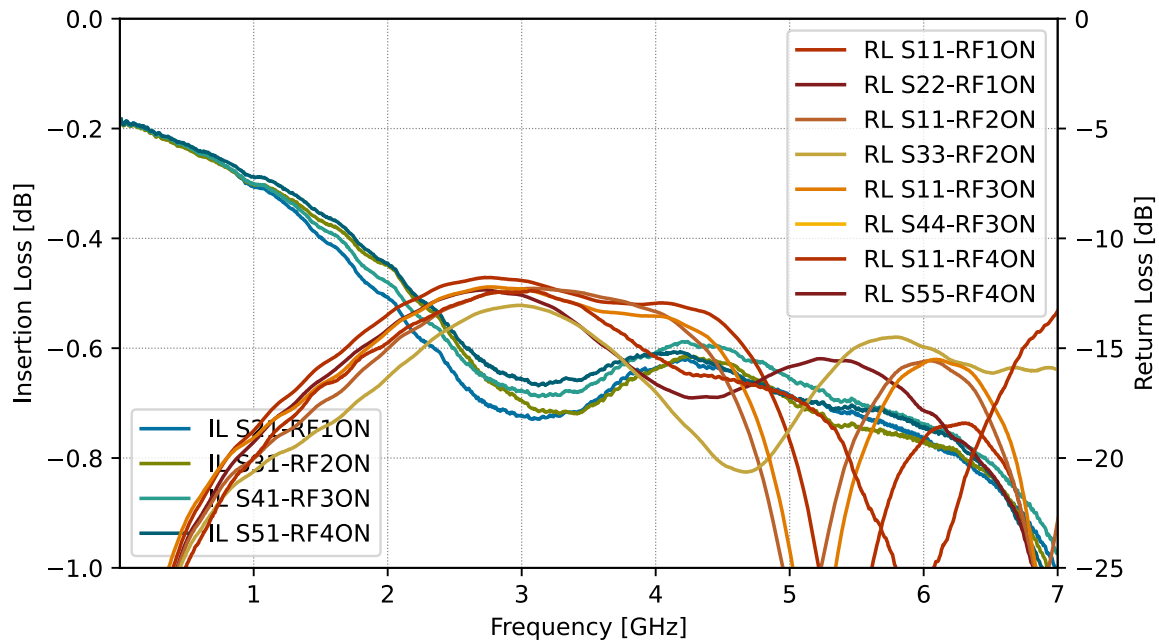
Matching of active port



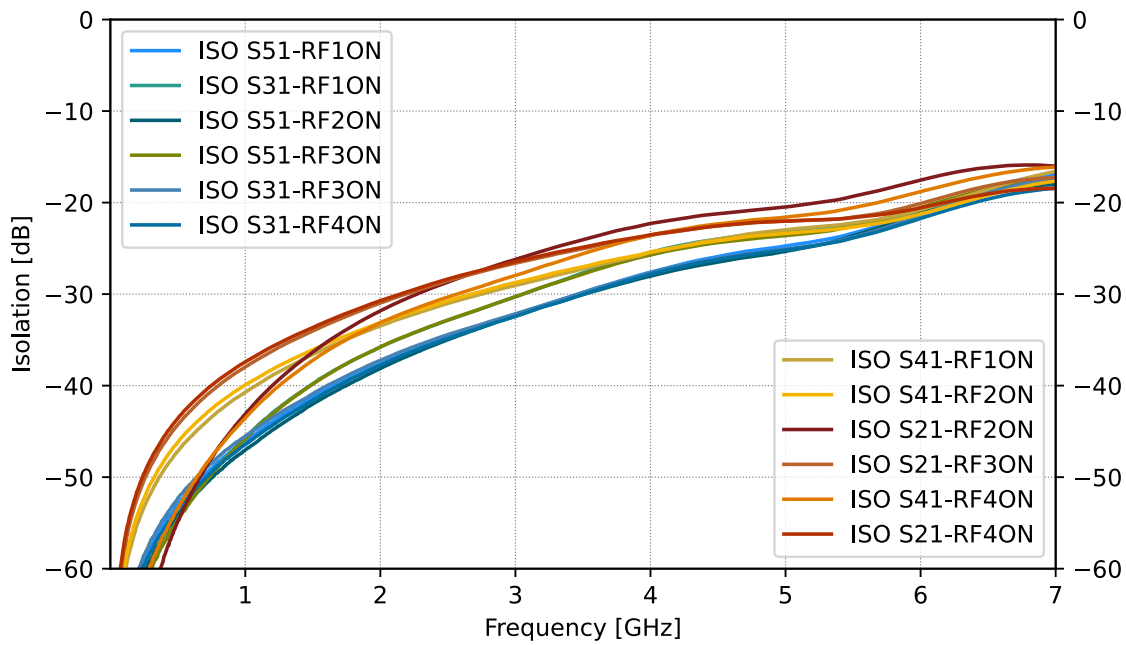
Termination impedance of non-active RFx.

Performance upto 6.0 GHz, matching applied to EVK

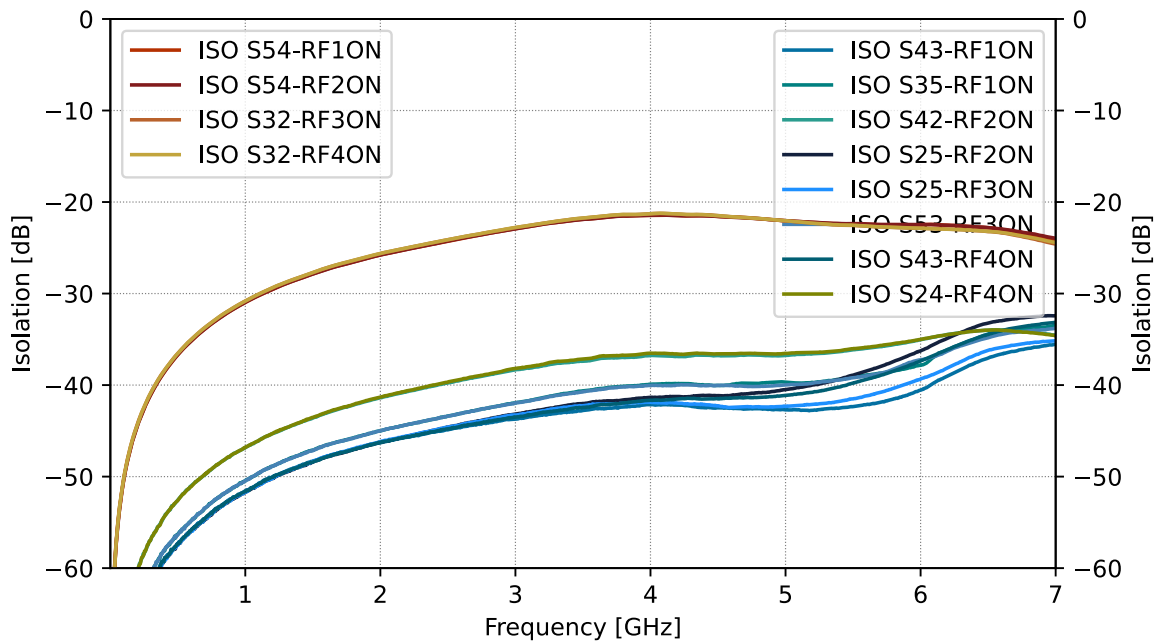
These measurements have been taken from TS8242FK EVK, matching components applied. CPW losses have been de-embedded from the measurements, but matching component losses are present.



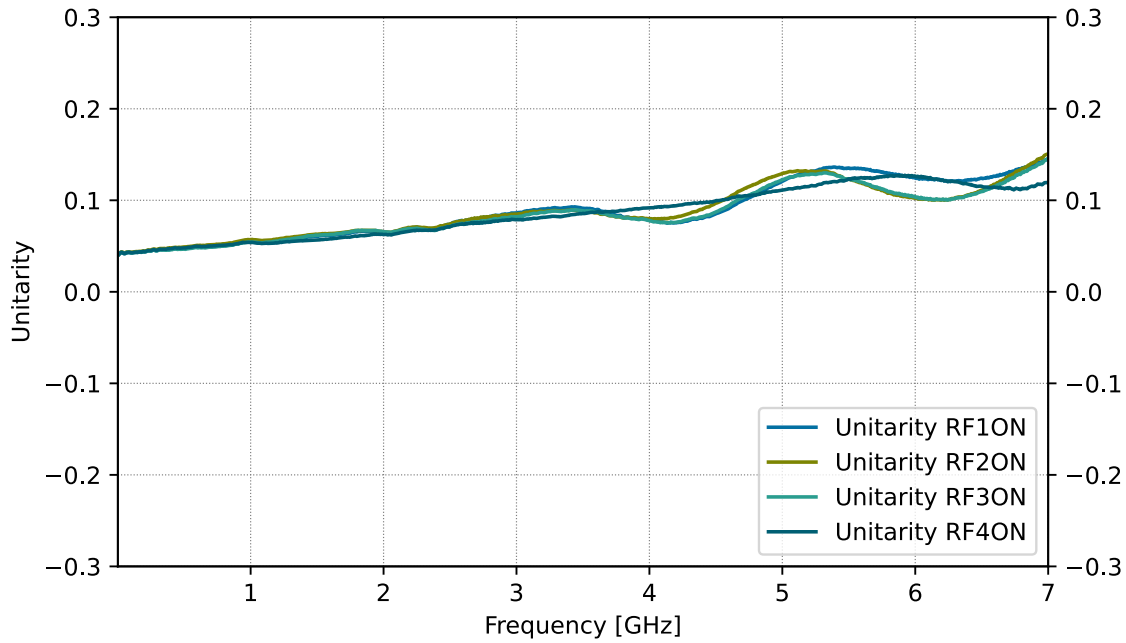
Insertion loss and Return loss, RFC – RFx.



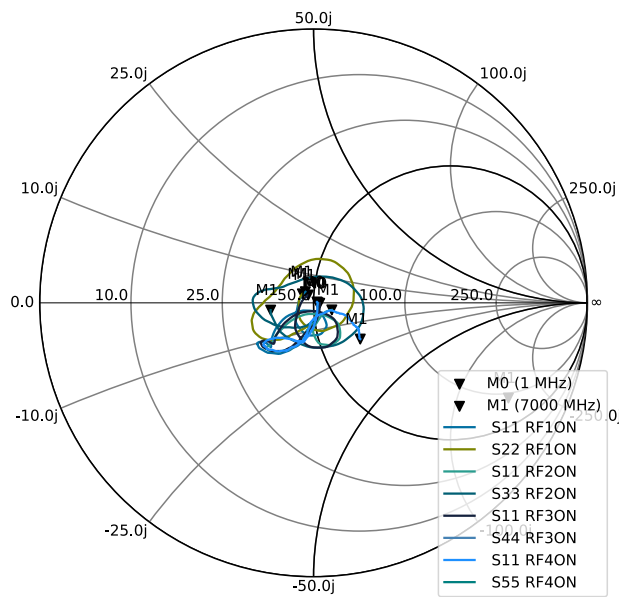
RFC – RFx isolation of non-active ports.



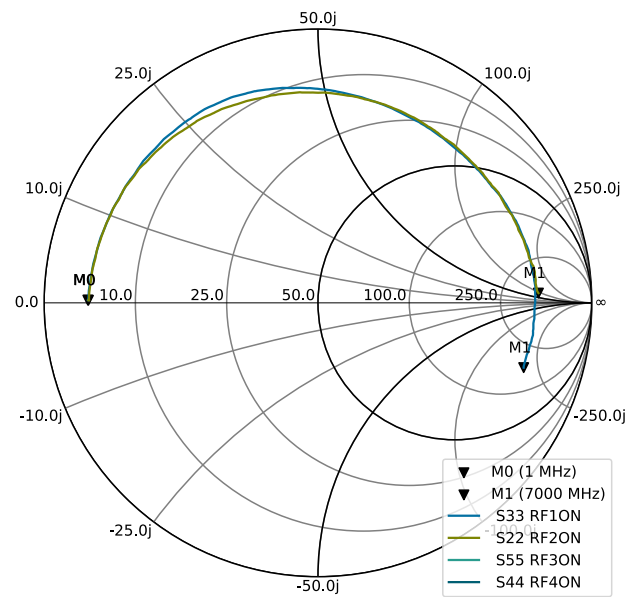
RFx – RFx isolation of non-active ports. Red/orange color curves are adjacent paths.



Unitarity, power absorption of the component, $1 - |S_{11}|^2 - |S_{21}|^2 - |S_{31}|^2 - |S_{41}|^2 - |S_{51}|^2$



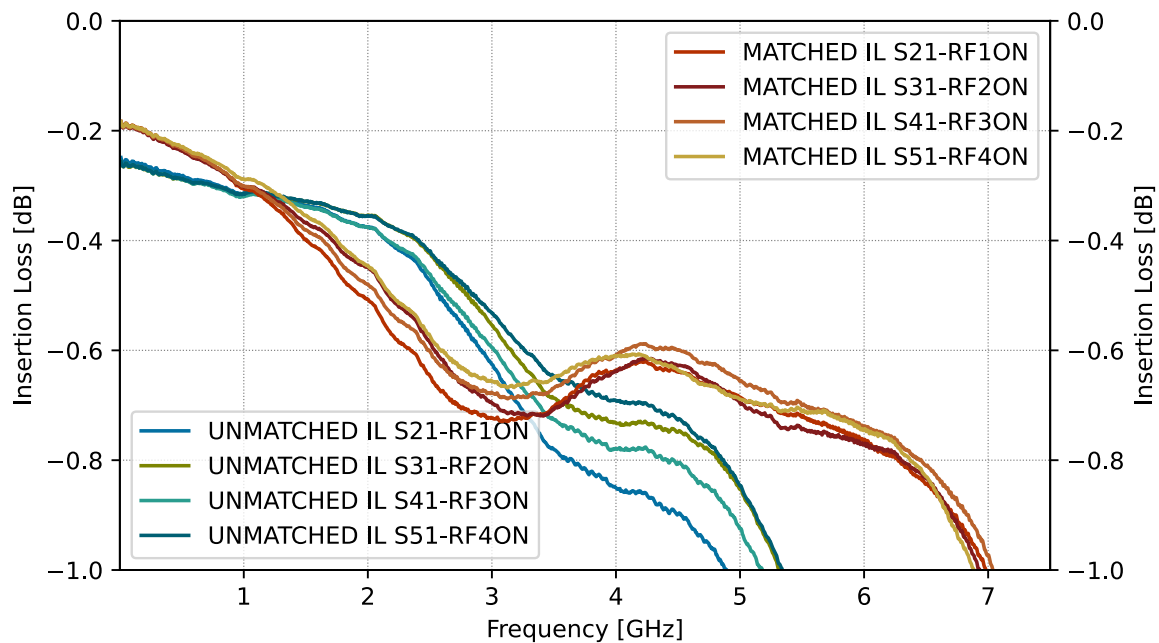
Matching of active port



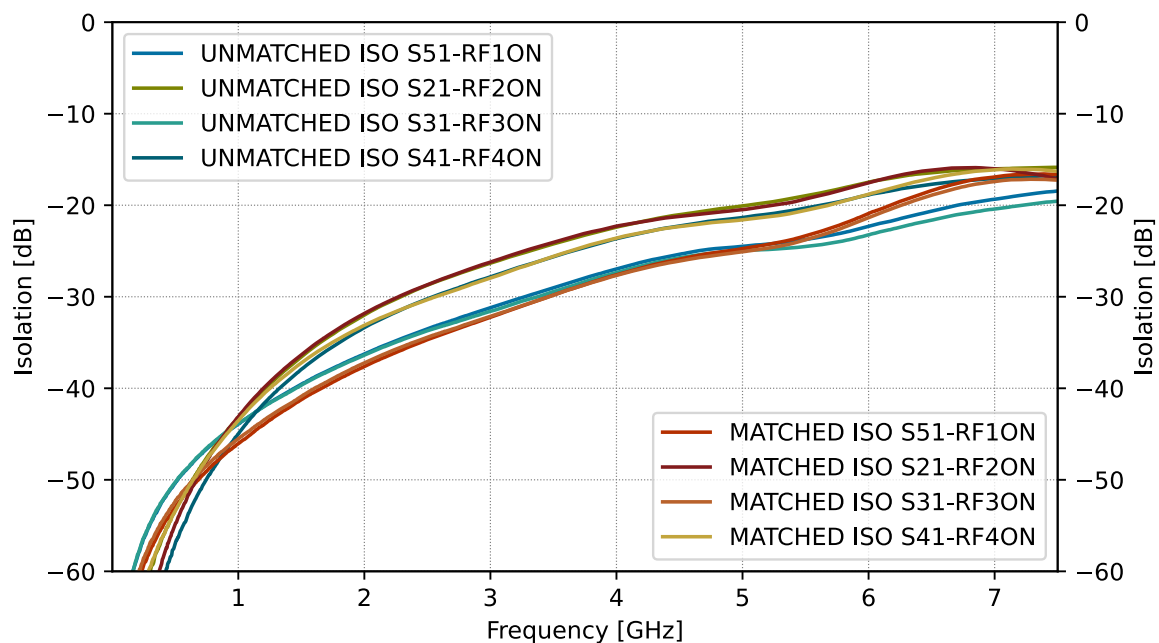
Termination impedance of non-active RFx.

Comparison plots of matched and unmatched switch.

Below are Insertion Loss and Isolation comparison plots of matched and unmatched switch. Matching extends frequency response to 6.0 GHz without affecting isolation.



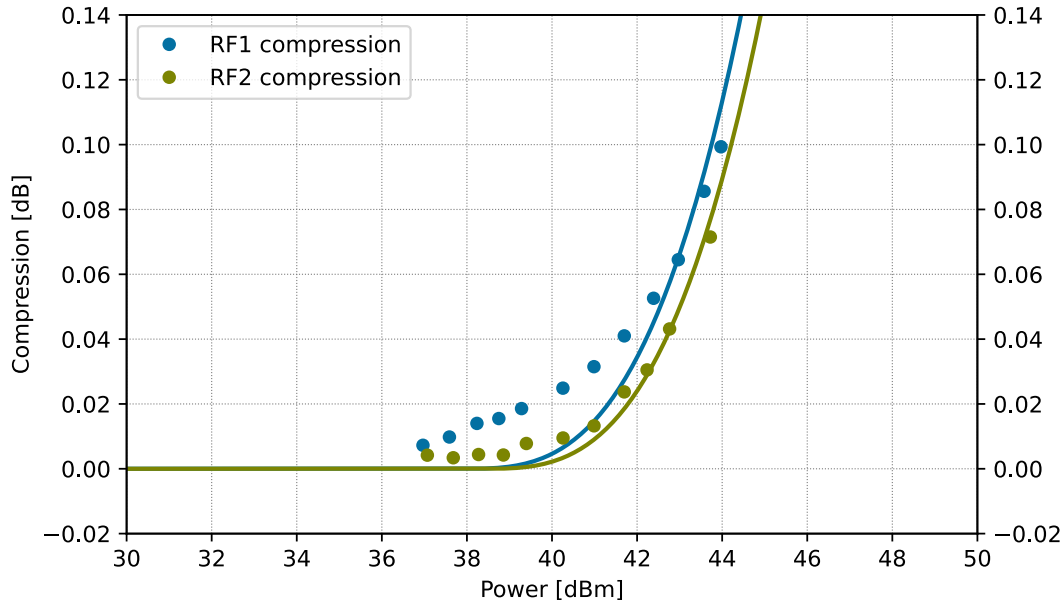
Insertion loss comparison of matched to 6.0 GHz and unmatched switch.



Isolation comparison of matched to 6.0 GHz and unmatched switch.

Compression measurement

In TagoreTech RF switches, compression is primarily attributed to thermal effects resulting from increased ohmic losses within the device. TS8242FK switch exhibits no signal clipping at the 0.1 dB compression point. All measurements were conducted at ambient temperature $T_A = +25^\circ\text{C}$. The presented data represents the average of three device samples. Measured data points are indicated by dots (•), while modeled predictions and extrapolations are shown as dashed lines (–). Test frequency 800 MHz.



0.1 dB Compression point measurement at room temperature, 800 MHz test frequency.

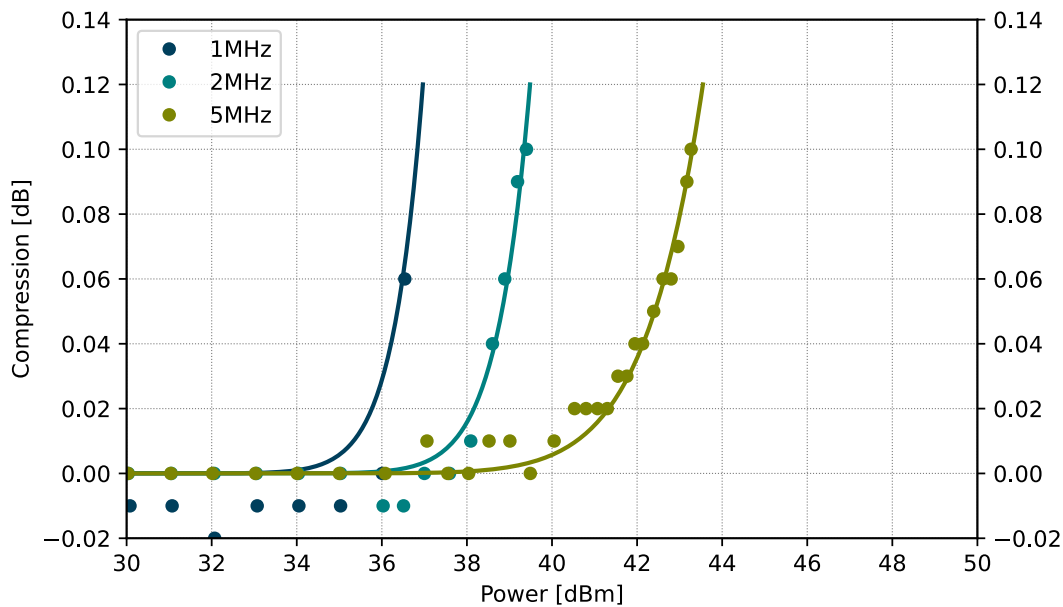
Power Derating

The TS8242FK exhibits power handling derating below 30 MHz. A power derating table has been established specifically for a 50-ohm environment. The measured 0.1 dB compression points at low frequencies - namely 1 MHz, 2 MHz, 5 MHz, and 10 MHz - were tested under controlled conditions at a room temperature of $T_A = +25^\circ\text{C}$.

Table 13: Power Derating table

Start f	Stop f	Max Power	Unit
1 MHz	2 MHz	34	dBm
2 MHz	5 MHz	36	dBm
5 MHz	10 MHz	40	dBm
10 MHz	f_{max}	40	dBm

TS8242FK Continuous Wave (CW) compression measurements are presented. Measurements are conducted at room temperature $T_A = +25^\circ\text{C}$. Values of the De-Rating table take into account manufacturing tolerances and margins. Measurements are presented as dot (•) and model and extrapolations presented as line (—).



TS8242FK CW Compression measurement at room temperature $T_A = +25^\circ\text{C}$.

Device Package information

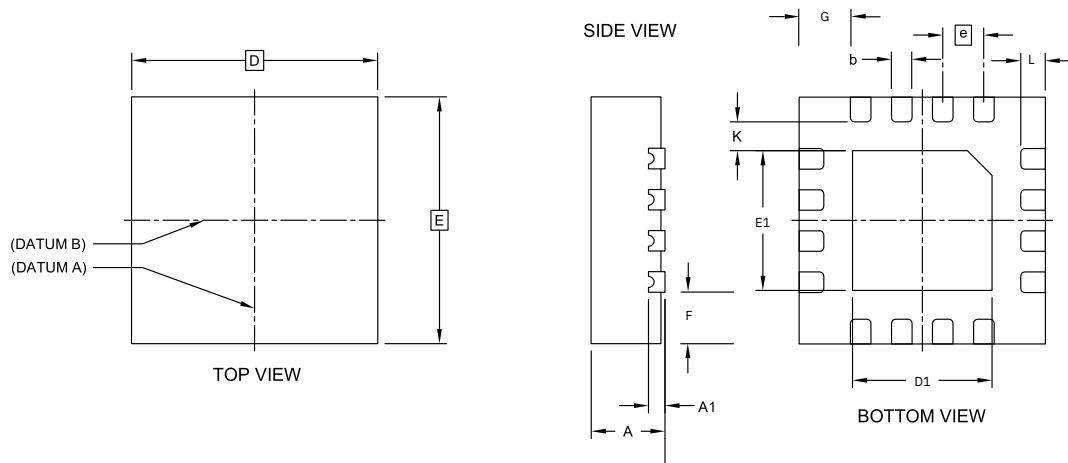


Figure 8: 16-pin QFN 3.0 x 3.0 x 0.75 mm³ package drawing.

Please refer to application notes TN-001 and TN-002 at TagoreTech web page for PCB and soldering guidelines.

Table 14: Device Package Dimensions

Dimension	Value [mm]	Tolerance [mm]	Dimension	Value [mm]	Tolerance [mm]
A	0.75	±0.05	E	3.00 BSC	±0.05
A1	0.203	±0.02	E1	1.70	±0.05
b	0.25	+0.05/-0.07	F	0.625	±0.05
D	3.00 BSC	±0.05	G	0.625	±0.05
D1	1.70	±0.05	L	0.25	±0.05
e	0.50 BSC	±0.05	K	0.40	±0.05

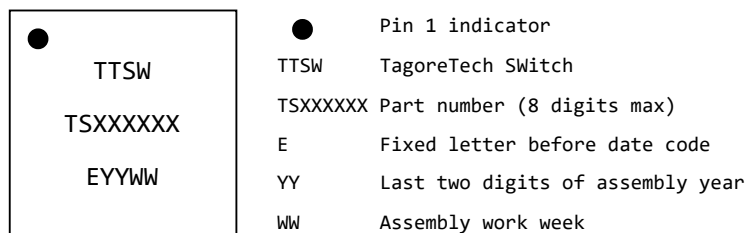


Figure 9: Part marking specification.

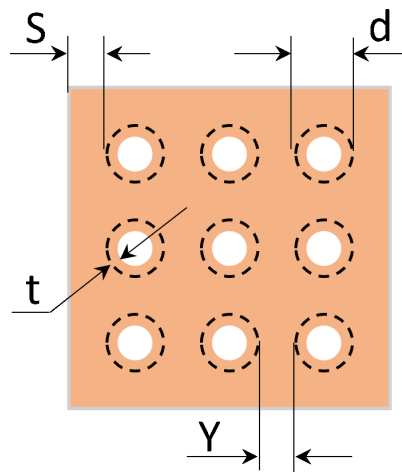
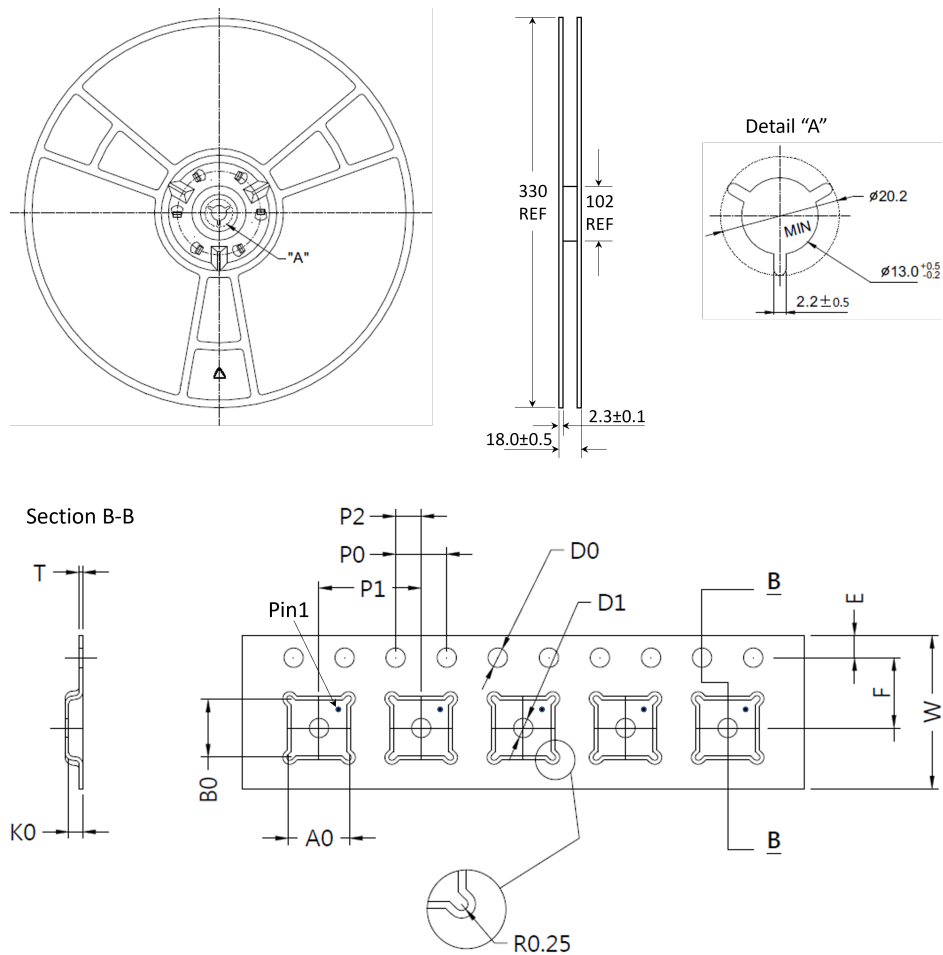


Figure 13: Thermal Via Pattern, Recommended Values: $S \geq 0.15\text{mm}$; $Y \geq 0.20\text{mm}$; $d = 0.2\text{mm}$; Plating Thickness $t = 25\mu\text{m}$ or $50\mu\text{m}$.

Tape and Reel Information



A0[mm]	B0[mm]	D0[mm]	D1[mm]	E[mm]	F[mm]	K0[mm]	P0[mm]	P1[mm]	P2[mm]	T[mm]	W[mm]
3.30	3.30	1.50	1.50	1.75	5.50	1.10	4.00	8.00	2.00	0.30	12.00

Glossary

IL	Insertion loss
ISO	Isolation
RL	Return loss
VSWR	Voltage Standing Wave Ratio
RFC	RF Common port, sometimes referred to as ANT
RFx	RF Port number x
Unitarity	Describes power absorption of the component, $1 - S_{11} ^2 - S_{21} ^2 - S_{31} ^2 - S_{41} ^2 - S_{51} ^2$ here with SP4T

Changelog

Table 15: Changelog

Date	Revision	Notes
03/31/2026	3.0	New release with updated information, frequency range extended to 6.0GHz
05/18/2026	3.01	Updated power de-rating table, measurement added and switching time pulse repetition rate defined
06/01/2026	3.02	Compression measurement at 800 MHz added.
06/25/2026	3.03	Table of Content added and a few typos fixed.
09/21/2026	3.04	Package thickness corrected to 0.75 mm, V_{CP} absolute maximum rating added, legal page updated, typos fixed.

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